

SPECIFICATION OF INFRARED LED CHIP

CN870-35P

[INFRARED]

1) Commodity Type and Physical Characteristics.

1. Material	GaAlAs/GaAlAs(DDH)		
2. Electrode	Top Side	P (anode) side	: Au Alloy
	Bottom Side	N (cathode) side	: Au Alloy
3. Electrode Pattern	Fig.1		
4. Chip Size	Fig.2		
5. Chip Thickness	Fig.2		
6. Emission Area	Fig.2		

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V_f	$I_f=20\text{mA}$		1.45	1.7	V
Reverse Current	I_r	$V_r=5\text{V}$			10	μA
Power Intensity	P_o	$I_f=20\text{mA}$	3.0	4.5		mW
Peak Wavelength	λ_P	$I_f=20\text{mA}$	860	870	880	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	$I_f=20\text{mA}$		40		nm
Rise Time	t_r	$I_f=20\text{mA}$		15		ns
Full time	t_f	$I_f=20\text{mA}$		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: μm]

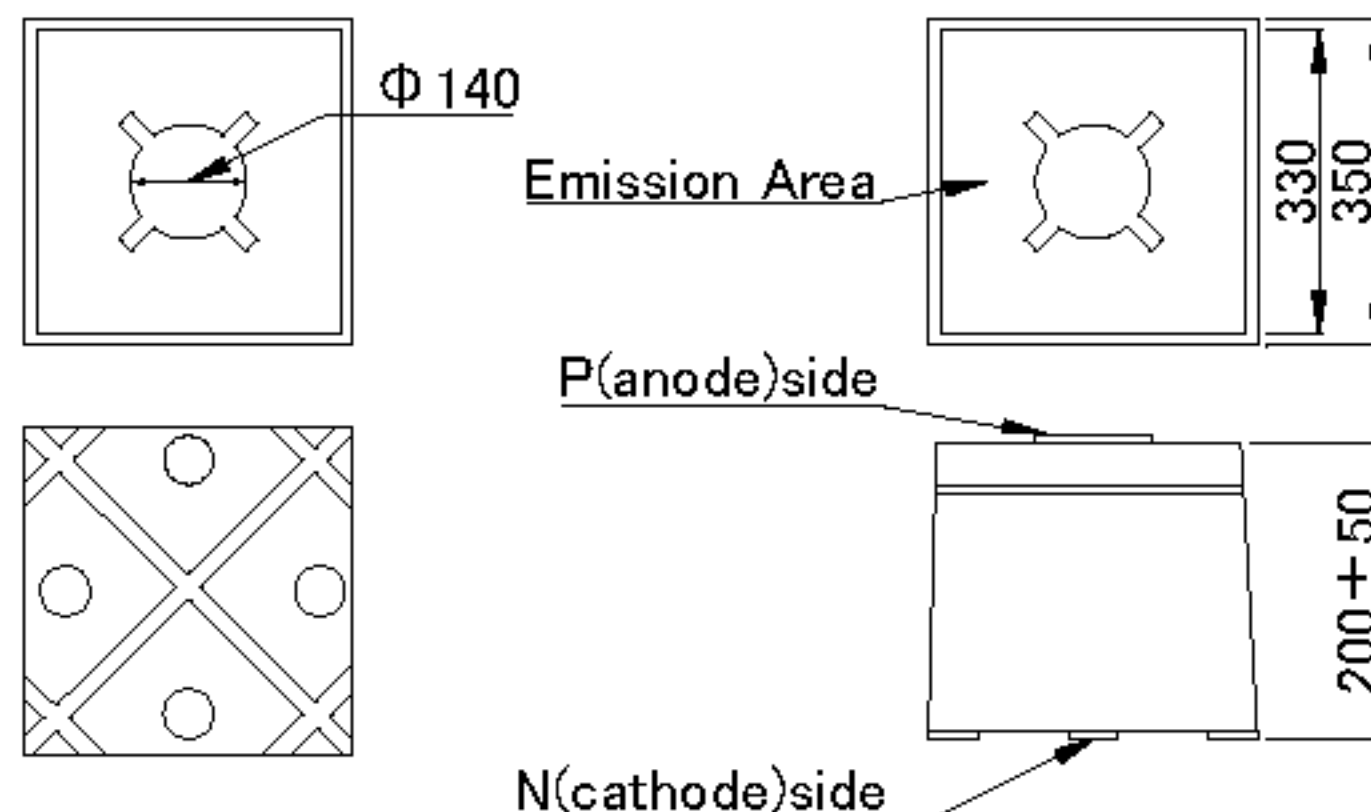


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area